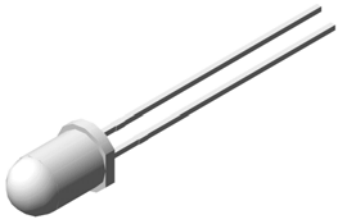
5mm Round 850nm Infrared Emitting Diode

UT 5468

Description

The UT 5468 used high efficiency 850nm GaAlAs materials molded into water clear lens. Comparing conventional GaAs/GaAs technology under similar wavelength, GaAlAs offers much higher radiant power. The viewing angles being offered is 40 degree. The most suitable application is Infrared radiation source for CMOS cameras.



Applications

- Infrared radiation source for CMOS cameras
- Free air transmission system
- Infrared applied system

RoHS

Pb
pb-free

Electronic Optical Characteristics (at 20mA):

Part Number	λ (nm)		Lens Color	mW/sr		View Angle	VF(V)	
	λp	△λ		Min.	Typ.	(2θ1/2)	Typ.	Max.
UT 5468	850	45	Water Clear	6.0	16	40	1.4	1.7

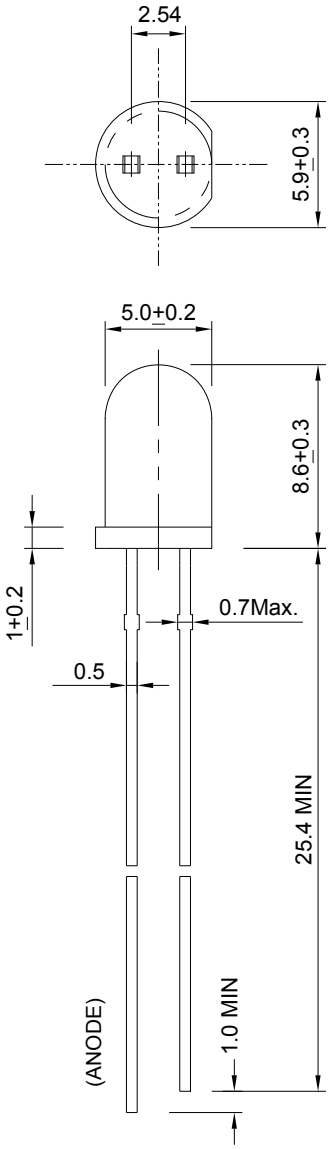
＊Radiant Intensity Typ. 100 mW/sr @ IF=100mA, Pulse Width ≦100μsec, Duty ≦1%, VF @ 2.40 Max.

Absolute Maximum Ratings (at Ta=25℃)

Parameter	Symbol	Rating	Unit	Condition
Continuous Forward Current	IF	100	mA	
Peak Forward Current	IP	1.0	A	Pulse width=100us Duty Cycle = 1%
Soldering Temperature	Tsol	260	℃	4mm from lens body 1ess than 5 seconds
Storage Temperature	Tstg	-40 - +85	℃	
Operating Temperature	Topr	-25 - +85	℃	
Power Dissipation	PD	150	mW	25°C Free Air Temperature

Package Dimension:

unit: mm



Notes:

1. All dimensions are millimeters.
2. Tolerance is ± 0.2mm unless otherwise specified.
3. Specifications are subject to change without notice.

Optical Characteristics Curves